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(54) **Title:** METHOD OF MANUFACTURING A STRUCTURE COMPRISING A SUBSTRATE AND A LAYER DEPOSITED ON ONE OF ITS FACES

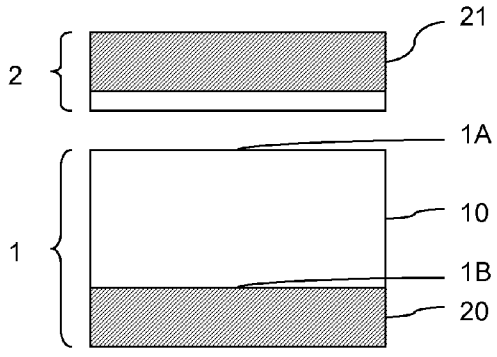


FIG. 6

(57) **Abstract:** The present invention relates to a method of fabricating a structure (1) for electronics, optics, optoelectronics or photovoltaics, the structure (1) comprising a substrate (10) and a layer (20) formed by depositing a material on one of the faces of the substrate (10), this method being characterized in that it comprises the steps of : - formation of a embrittled substrate comprising a embrittlement zone defining, on the one hand, said substrate (10) and, on the other hand, a remainder, - deposition of a layer (20,21) of said material on each one of the two faces of the embrittled substrate, - cleavage of the embrittled substrate, so as to form the structure (1) in which face (IB) of the substrate (10) is covered with the layer (20) of the material deposited while its other face (IA) is exposed.

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